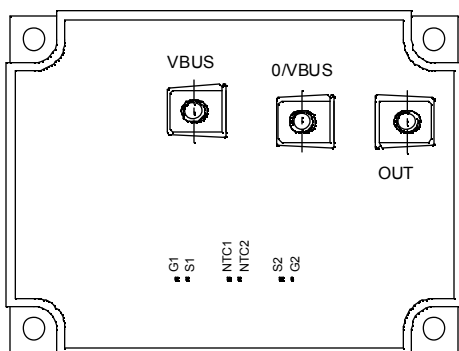
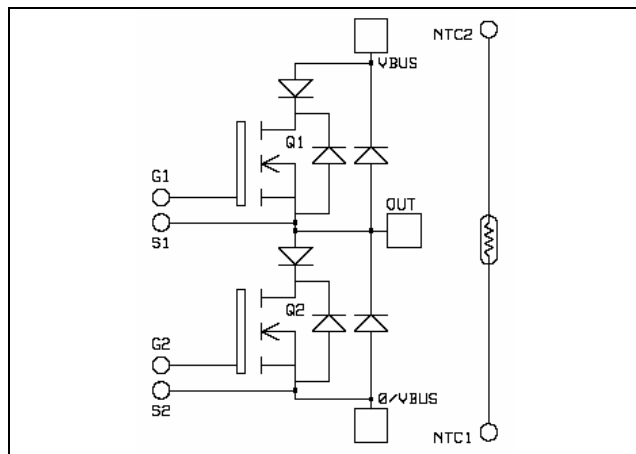


*Phase leg
Schottky Series &
parallel diodes
MOSFET Power Module*

$$V_{DSS} = 1000V$$

$$R_{DSon} = 120m\Omega \text{ max @ } T_j = 25^\circ C$$

$$I_D = 68A \text{ @ } T_c = 25^\circ C$$



Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals for signal and M5 for power for easy PCB mounting

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	270	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	120	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	18	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 750\mu A$	1000			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V, T_j = 25^\circ\text{C}$			200	μA
		$V_{GS} = 0V, V_{DS} = 800V, T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 34A$			120	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10mA$	3		5	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		17.4		nF
C_{oss}	Output Capacitance			2.86		
C_{rss}	Reverse Transfer Capacitance			0.48		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 500V$ $I_D = 68A$		616		nC
Q_{gs}	Gate - Source Charge			104		
Q_{gd}	Gate - Drain Charge			388		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 667V$ $I_D = 68A$ $R_G = 1.2\Omega$		10		ns
T_r	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			121		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 667V$ $I_D = 68A, R_G = 1.2\Omega$		2556		μJ
E_{off}	Turn-off Switching Energy ❷			1520		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 667V$ $I_D = 68A, R_G = 1.2\Omega$		4148		μJ
E_{off}	Turn-off Switching Energy ❷			1804		

Series Schottky diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle $T_c = 85^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60A$		0.77		V
		$I_F = 60A, T_j = 125^\circ\text{C}$		0.62		

❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	$T_c = 100^\circ\text{C}$		120		A
V_F	Diode Forward Voltage	$I_F = 120\text{A}$			1.9	2.5	V
		$I_F = 240\text{A}$			2.2		
		$I_F = 120\text{A}$	$T_j = 125^\circ\text{C}$		1.7		
t_{rr}	Reverse Recovery Time	$I_F = 120\text{A}$ $V_R = 667\text{V}$ $di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		280		ns
			$T_j = 125^\circ\text{C}$		350		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		1520		nC
			$T_j = 125^\circ\text{C}$		7200		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case	Transistor				0.1	$^\circ\text{C}/\text{W}$
		Series Diode				1	
		Parallel diode				0.46	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$, $I_{isol} < 1\text{mA}$, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M5	2		3.5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					620	g

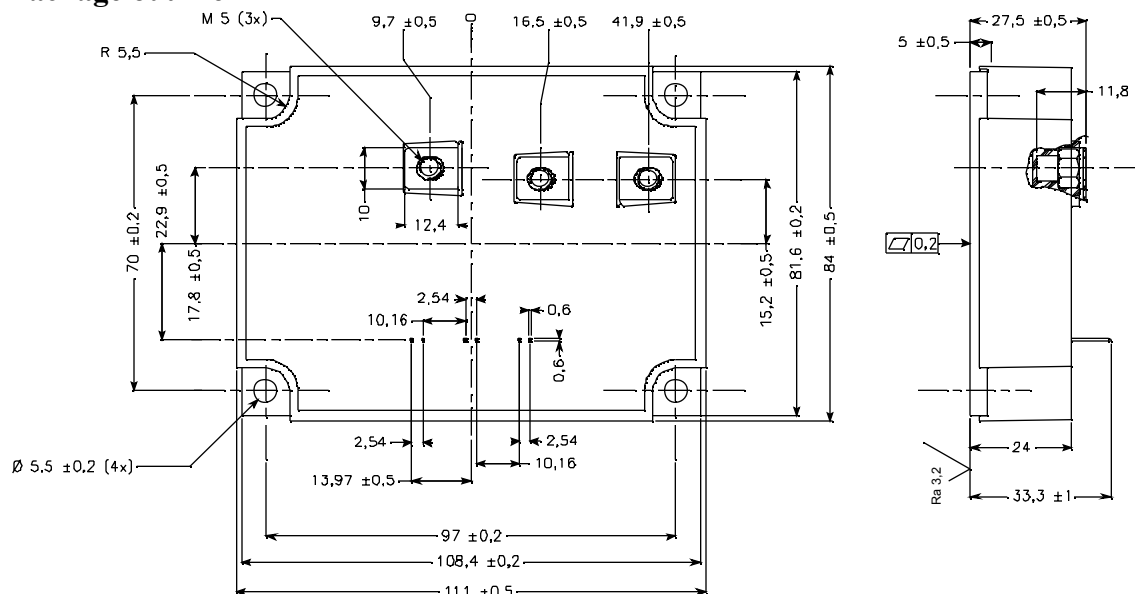
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		$\text{k}\Omega$
$B_{25/85}$	$T_{25} = 298.16\text{ K}$		4080		K

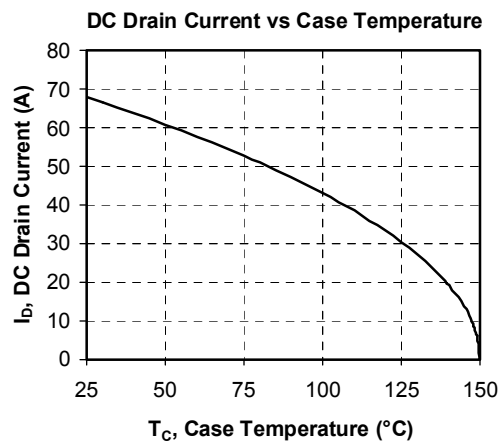
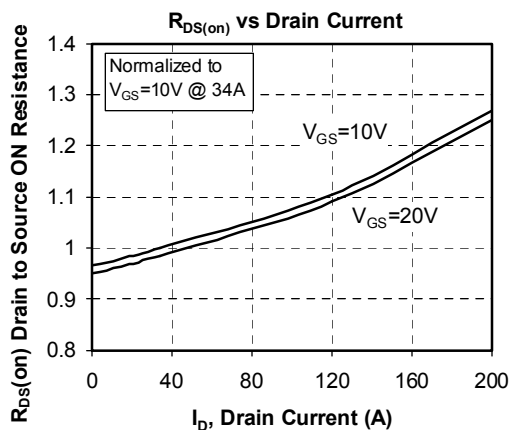
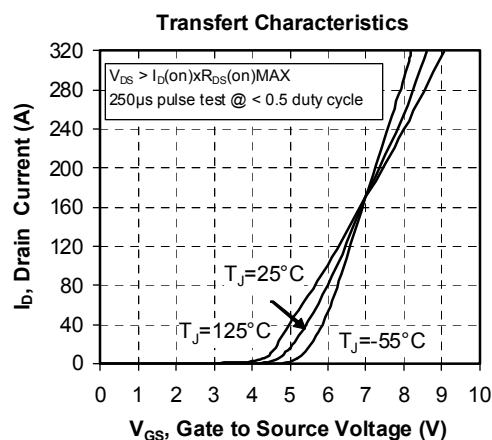
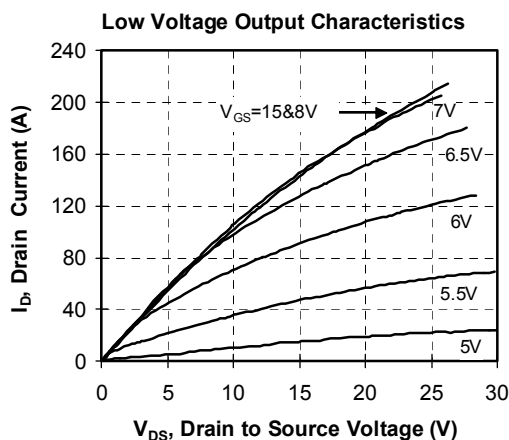
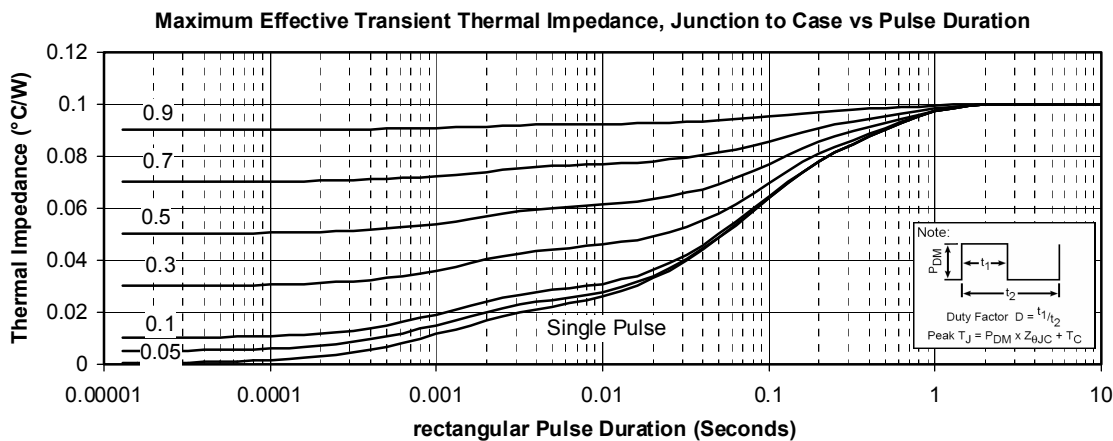
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

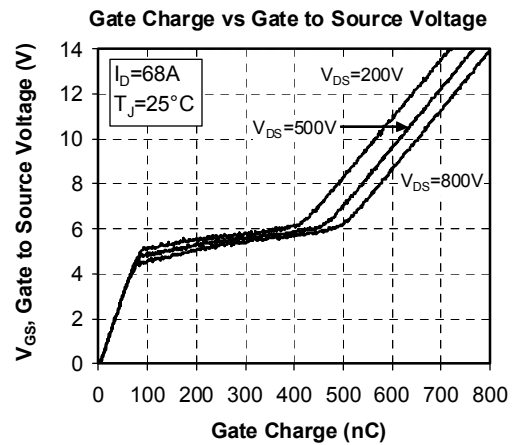
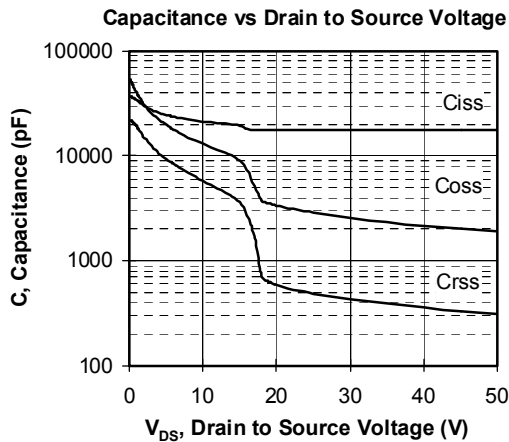
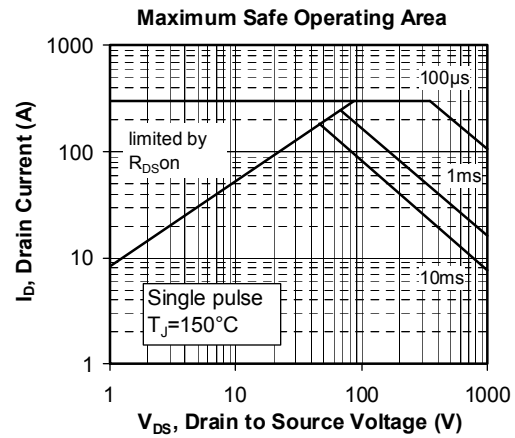
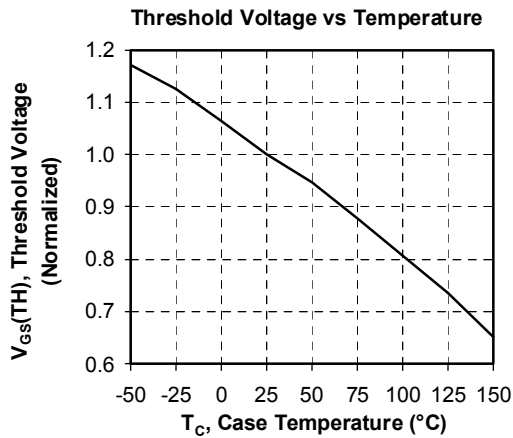
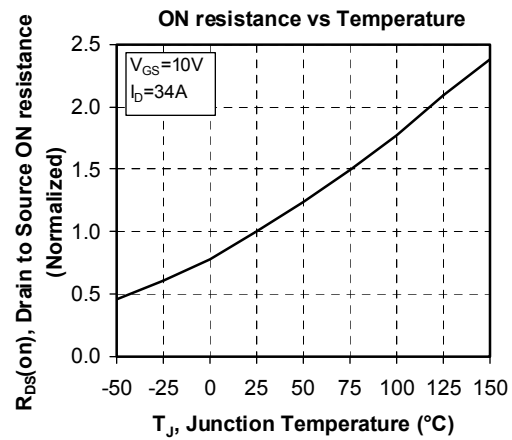
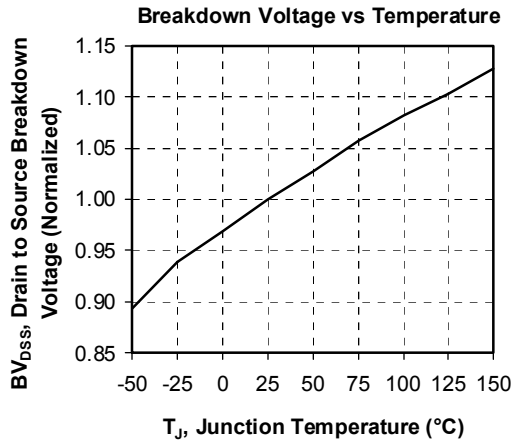
T: Thermistor temperature
R_T: Thermistor value at T

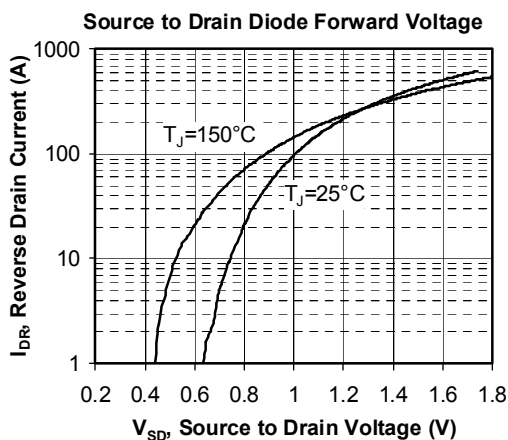
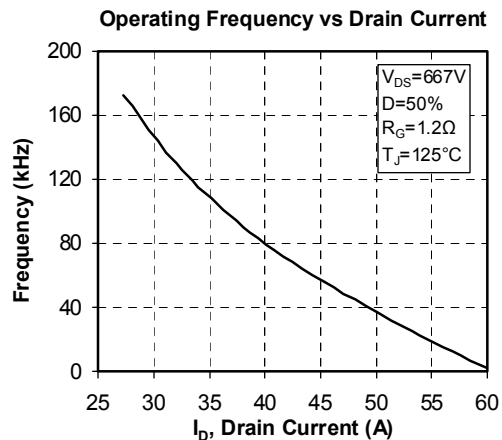
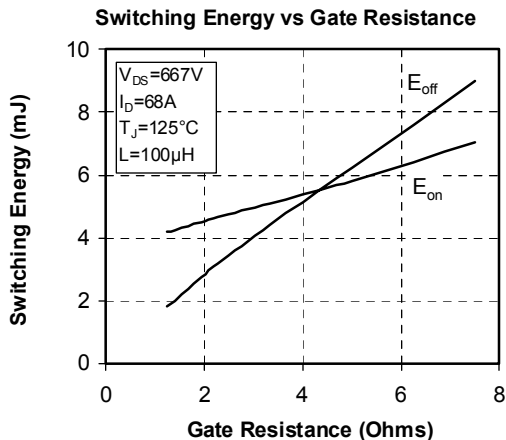
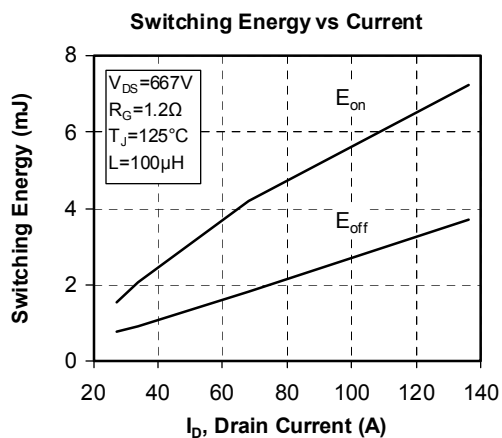
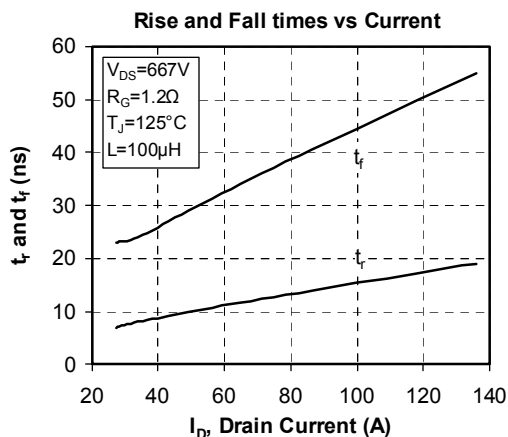
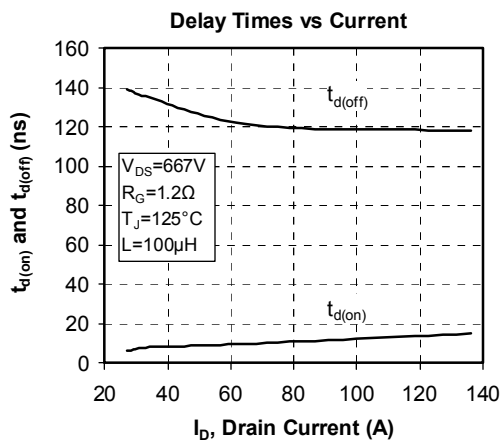
Package outline



Typical Performance Curve







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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.